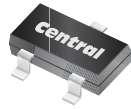


CMPDM7002AHC
SURFACE MOUNT
N-CHANNEL
ENHANCEMENT-MODE
SILICON MOSFET



www.centrasemi.com



SOT-23 CASE

• Device is **Halogen Free** by design

APPLICATIONS:

- Load/Power Switches
- Power Supply Converter Circuits
- Battery Powered Portable Equipment

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPDM7002AHC is a High Current version of the 2N7002A Enhancement-mode N-Channel MOSFET, designed for high speed pulsed amplifier and driver applications.

MARKING CODE: 702H

FEATURES:

- ESD Protection up to 2kV
- 350mW Power Dissipation
- Low $r_{DS(ON)}$: 0.22 Ω MAX @ $V_{GS}=10V$
- Industry Standard SOT-23 Surface Mount Package

MAXIMUM RATINGS: ($T_A=25^\circ C$)

Drain-Source Voltage
Drain-Gate Voltage
Gate-Source Voltage
Continuous Drain Current (Steady State)
Maximum Pulsed Drain Current (tp=10 μ s)
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_{DS}	60
V_{DG}	60
V_{GS}	20
I_D	1.0
I_{DM}	5.0
P_D	350
T_J, T_{stg}	-65 to +150
Θ_{JA}	357

UNITS

V
V
V
A
A
mW
$^\circ C$
$^\circ C/W$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ C$ unless otherwise noted)

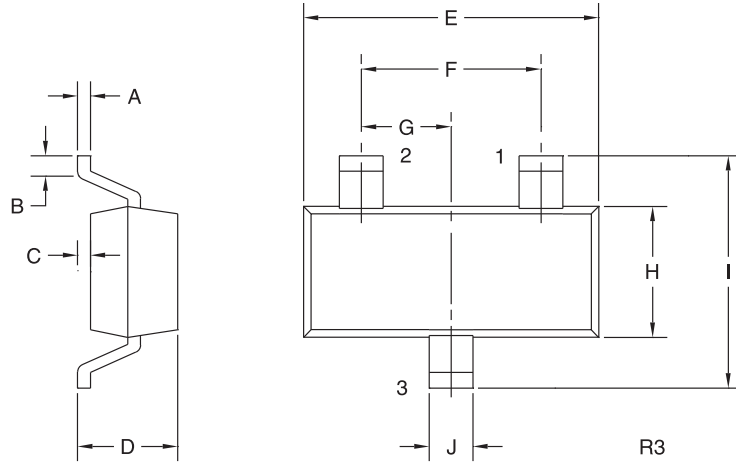
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{GSSF}, I_{GSSR}	$V_{GS}=20V, V_{DS}=0$			10	μA
I_{DSS}	$V_{DS}=60V, V_{GS}=0$			500	nA
BV_{DSS}	$V_{GS}=0, I_D=100\mu A$	63			V
$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2		2.3	V
V_{SD}	$V_{GS}=0, I_S=500mA$			0.9	V
$r_{DS(ON)}$	$V_{GS}=10V, I_D=500mA$		0.15	0.22	Ω
$r_{DS(ON)}$	$V_{GS}=5.0V, I_D=500mA$		0.20	0.30	Ω
$Q_g(tot)$	$V_{DS}=10V, V_{GS}=4.5V, I_D=1.0A$		2.3		nC
Q_{gs}	$V_{DS}=10V, V_{GS}=4.5V, I_D=1.0A$		1.0		nC
Q_{gd}	$V_{DS}=10V, V_{GS}=4.5V, I_D=1.0A$		0.7		nC
C_{rss}	$V_{DS}=25V, V_{GS}=0, f=1.0MHz$			25	pF
C_{iss}	$V_{DS}=25V, V_{GS}=0, f=1.0MHz$			240	pF
C_{oss}	$V_{DS}=25V, V_{GS}=0, f=1.0MHz$			50	pF
t_{on}	$V_{DD}=30V, V_{GS}=4.5V, I_D=1.0A$ $R_G=6.0\Omega, R_L=30\Omega$			35	ns
t_{off}	$V_{DD}=30V, V_{GS}=4.5V, I_D=1.0A$ $R_G=6.0\Omega, R_L=30\Omega$			50	ns

R2 (2-August 2011)

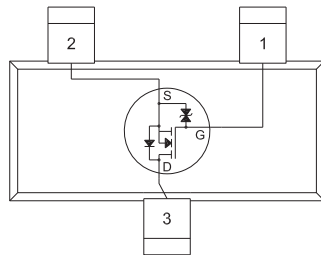
CMPDM7002AHC
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SOT-23 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

LEAD CODE:

- 1) Gate
- 2) Source
- 3) Drain

MARKING CODE: 702H

R2 (2-August 2011)